

Please rewrite the paragraph at page 8, lines 12-17, so that it reads as follows:

Unillustrated plural circuit elements are formed on a surface 109 (first main surface) of a semiconductor substrate 103 made up of silicon. A steplike section 107 is provided at the back 105 (second main surface) of the semiconductor substrate 103. An insulating layer 402 having contact holes (not shown) is formed over the respective circuit elements. An unillustrated conductive layer is formed inside each contact hole.

IN THE CLAIMS:

Kindly cancel claims 1-55, and add in lieu thereof the following new claims 56-74:

56. A semiconductor device comprising:
a semiconductor chip having a plurality of electrode pads;
a molding resin structure covering the semiconductor chip, the molding resin structure having a first main surface and a second main surface opposite to the first main surface;
a plurality of terminals formed on the first main surface of the structure, the terminals being electrically connected to the electrode pads, respectively; and
a stripe groove formed on the second main surface of the structure, wherein the stripe groove divides the second main surface asymmetrically.
57. A semiconductor device according to claim 56, wherein the stripe groove has a V shaped profile.
58. A semiconductor device according to claim 56, wherein the stripe groove has a U shaped profile.
59. A semiconductor device according to claim 56, further comprising an auxiliary stripe groove formed on the second main surface of the structure, wherein the stripe groove and the auxiliary stripe groove intersect at an off-center point.
60. A semiconductor device according to claim 56, further comprising an auxiliary stripe groove formed on the second main surface of the structure, wherein the

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auxiliary stripe groove is parallel to the stripe groove, and wherein the auxiliary stripe groove divides the second main surface asymmetrically.

61. A semiconductor device according to claim 56, wherein the terminals are arranged in a plurality of rows.

62. A semiconductor device according to claim 61, wherein the stripe groove is formed at a position corresponding to one of the rows of the terminals.

63. A semiconductor device comprising:
a semiconductor chip having a plurality of electrode pads;
a molding resin structure covering the semiconductor chip, the molding resin structure having a first main surface and a second main surface opposite to the first main surface, the second main surface having four sides;
a plurality of terminals formed on the first main surface of the structure, the terminals being electrically connected to the electrode pads, respectively; and
a steplike section formed on one of the sides of the second main surface of the structure.

64. A semiconductor device according to claim 63, wherein a thickness of the structure at the steplike section becomes smaller approaching the one of the edges.

65. A semiconductor device according to claim 63, further comprising an auxiliary steplike section formed on the other one of the sides of the second main surface of the structure wherein the auxiliary steplike section and the steplike section intersect at a corner of the main surface.

66. A semiconductor device according to claim 63, wherein the terminals are arranged in a plurality of rows.

67. A semiconductor device comprising:
a semiconductor chip having a plurality of electrode pads;
a sealing resin structure covering the semiconductor chip, the sealing resin structure having a first main surface and a second main surface opposite to the first main surface, the second main surface having a first roughness;
a plurality of terminals formed on the first main surface of the structure, the terminals being electrically connected to the electrode pads, respectively; and
a stripe portion formed on the second main surface of the structure, the stripe portion having a second roughness that is coarser than the first roughness, wherein the stripe portion divides the second main surface asymmetrically.

68. A semiconductor device according to claim 67, wherein the stripe portion has a groove.

69. A semiconductor device according to claim 68, wherein the groove has a V shaped profile.

70. A semiconductor device according to claim 68, wherein the groove has a U shaped profile.

71. A semiconductor device according to claim 67, further comprising an auxiliary stripe portion formed on the second main surface of the structure, the auxiliary stripe portion substantially having the second roughness, wherein the stripe portion and the auxiliary stripe portion intersect at an off-center point.

72. A semiconductor device according to claim 67, further comprising an auxiliary stripe portion formed on the second main surface of the structure in parallel with the stripe portion, the auxiliary stripe portion substantially having the second roughness, wherein the auxiliary stripe portion divides the second main surface asymmetrically.

73. A semiconductor device according to claim 67, wherein the terminals are arranged in a plurality of rows.

74. A semiconductor device according to claim 73, wherein the stripe portion is formed at a position corresponding to one of the rows of the terminals.